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Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claim 1 (Original): A semiconductor device comprising:
at least one thin film transistor having an active layer comprising crystalline semiconductor film comprising silicon;
at least one circuit comprising said thin film transistor formed on a substrate having an insulating surface;
a plurality of wiring lines formed into said circuit; and
a plurality of wiring lines connected with said circuit,
wherein at least part of at least one of said wiring lines is electrically connected in parallel with an auxiliary wiring line through an interlayer insulating film.

Claims 2-9 (Canceled)

Claim 10 (New): A method of manufacturing a semiconductor device comprising:
forming a first wiring over a substrate;
forming an insulating film over the first wiring;
forming a plurality of contact holes in the insulating film; and
forming a second wiring over the insulating film,
wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and
wherein the first wiring extends in parallel with the second wiring.

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Claim 11 (New): A method of manufacturing a semiconductor device according to claim 10, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 12 (New): A method of manufacturing a semiconductor device according to claim 10, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 13 (New): A method of manufacturing a semiconductor device according to claim 10, wherein the second wiring comprises aluminum.

Claim 14 (New): A method of manufacturing a semiconductor device according to claim 10, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

Claim 15 (New): A method of manufacturing a semiconductor device comprising:
forming a first wiring on a same layer as a gate electrode over a substrate;
forming an insulating film over the first wiring and the gate electrode;
forming a plurality of contact holes in the insulating film; and
forming a second wiring on a same layer as a source or drain electrode over the insulating film,
wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and
wherein the first wiring extends in parallel with the second wiring.

Claim 16 (New): A method of manufacturing a semiconductor device according to claim 15, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

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Claim 17 (New): A method of manufacturing a semiconductor device according to claim 15, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 18 (New): A method of manufacturing a semiconductor device according to claim 15, wherein the second wiring comprises aluminum.

Claim 19 (New): A method of manufacturing a semiconductor device according to claim 15, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

Claim 20 (New): A method of manufacturing a semiconductor device comprising:
forming a first wiring in a driving circuit over a substrate;
forming an insulating film over the first wiring;
forming a plurality of contact holes in the insulating film; and
forming a second wiring in the driving circuit over the insulating film,
wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and
wherein the first wiring extends in parallel with the second wiring.

Claim 21 (New): A method of manufacturing a semiconductor device according to claim 20, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 22 (New): A method of manufacturing a semiconductor device according to claim 20, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

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Claim 23 (New): A method of manufacturing a semiconductor device according to claim 20, wherein the second wiring comprises aluminum.

Claim 24 (New): A method of manufacturing a semiconductor device according to claim 20, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

Claim 25 (New): A method of manufacturing a semiconductor device comprising:
forming a first wiring in a driving circuit on a same layer as a gate electrode over a substrate;

forming an insulating film over the first wiring and the gate electrode;

forming a plurality of contact holes in the insulating film; and

forming a second wiring in the driving circuit on a same layer as a source or drain electrode over the insulating film,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and

wherein the first wiring extends in parallel with the second wiring.

Claim 26 (New): A method of manufacturing a semiconductor device according to claim 25, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 27 (New): A method of manufacturing a semiconductor device according to claim 25, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

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Claim 28 (New): A method of manufacturing a semiconductor device according to claim 25, wherein the second wiring comprises aluminum.

Claim 29 (New): A method of manufacturing a semiconductor device according to claim 25, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

Claim 30 (New): A method of manufacturing a semiconductor device comprising:
forming a first wiring in a source line driving circuit over a substrate;
forming an insulating film over the first wiring;
forming a plurality of contact holes in the insulating film; and
forming a second wiring in the source line driving circuit over the insulating film,
wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and
wherein the first wiring extends in parallel with the second wiring.

Claim 31 (New): A method of manufacturing a semiconductor device according to claim 30, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 32 (New): A method of manufacturing a semiconductor device according to claim 30, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 33 (New): A method of manufacturing a semiconductor device according to claim 30, wherein the second wiring comprises aluminum.

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Claim 34 (New): A method of manufacturing a semiconductor device according to claim 30, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

Claim 35 (New): A method of manufacturing a semiconductor device comprising:
forming a first wiring in a source line driving circuit on a same layer as a gate electrode over a substrate;

forming an insulating film over the first wiring and the gate electrode;

forming a plurality of contact holes in the insulating film; and

forming a second wiring in the source line driving circuit on a same layer as a source or drain electrode over the insulating film,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and

wherein the first wiring extends in parallel with the second wiring.

Claim 36 (New): A method of manufacturing a semiconductor device according to claim 35, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 37 (New): A method of manufacturing a semiconductor device according to claim 35, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 38 (New): A method of manufacturing a semiconductor device according to claim 35, wherein the second wiring comprises aluminum.

Claim 39 (New): A method of manufacturing a semiconductor device according to claim 35, wherein the semiconductor device is at least one of a liquid crystal display device and an

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electroluminescence display device.

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